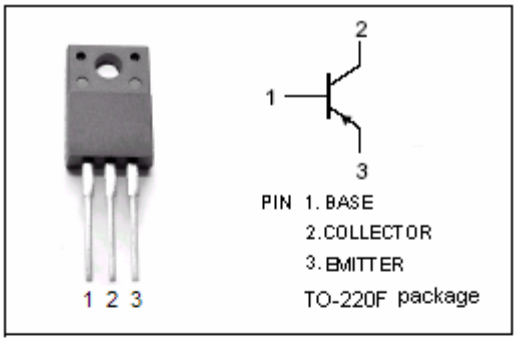
isc Silicon PNP Power Transistor 2SA1567

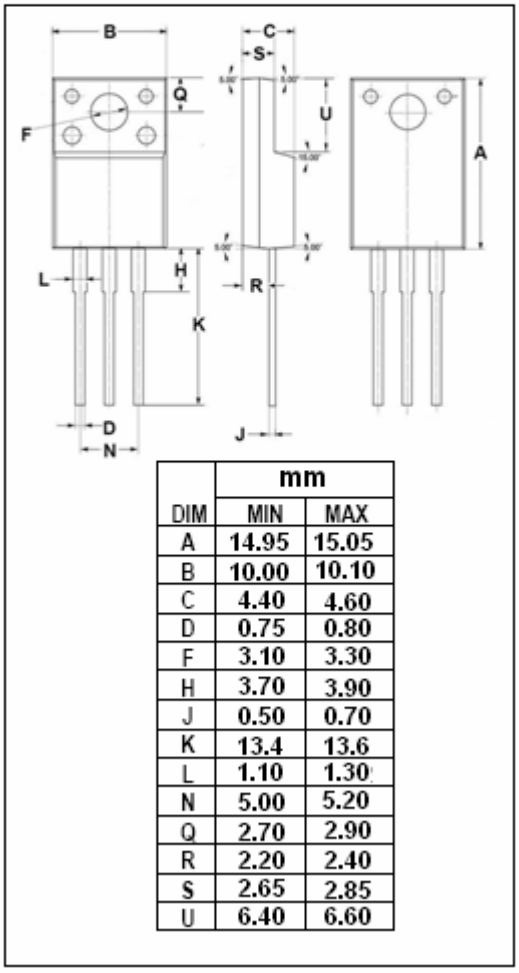
DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -50V(Min)
- DC Current Gain-
  : h_{FE}= 50(Min)@ (V_{CE}= -1V,I_C= -6A)
- Low Saturation Voltage-
  : $V_{CE(sat)}$= −0.35V(Max)@ (I_C= -6A, I_B -0.6A)



APPLICATIONS

- Designed for DC motor driver, chopper regulator and general purpose applications.



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-12	A
I_B	Base Current-Continuous	-3	A
P_C	Collector Power Dissipation @T_C=25℃	35	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -25mA ; I_B= 0	-50			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -6A; I_B= -0.3A			-0.35	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -50V ; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-100	μA
h_{FE}	DC Current Gain	I_C= -6A ; V_{CE}= -1V	50			
C_{OB}	Output Capacitance	I_E=0 ; V_{CB}= -10V;f_{test}= 1.0MHz		330		pF
f_T	Current-Gain—Bandwidth Product	I_E= 0.5A ; V_{CE}= -12V		40		MHz

Switching Times

t_{on}	Turn-on Time	I_C= -6A ,R_L= 4Ω , I_{B1}= -I_{B2}= -0.12A,V_{CC}≒ -24V		0.4		μs
t_{stg}	Storage Time			0.4		μs
t_f	Fall Time			0.2		μs